

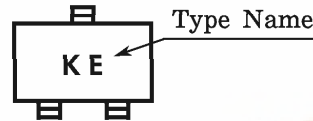
TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

2SK1062

HIGH SPEED SWITCHING APPLICATIONS
ANALOG SWITCHING APPLICATIONS
INTERFACE APPLICATIONS

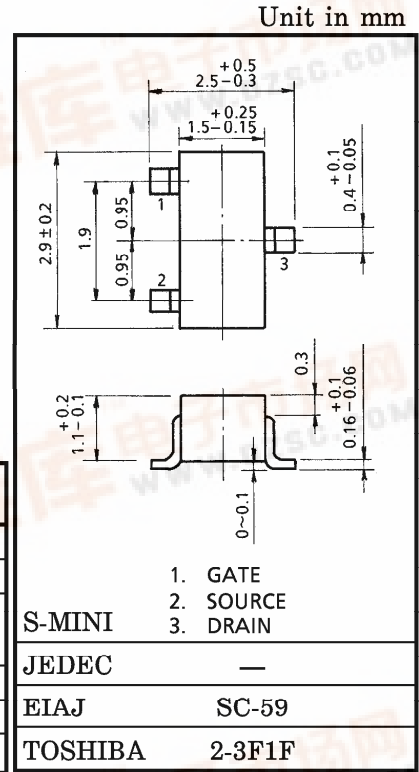
- Excellent Switching Time : $t_{on} = 14ns$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 100mS$ (Min.) @ $I_D = 50mA$
- Low On Resistance : $R_{DS(ON)} = 0.6\Omega$ (Typ.) @ $I_D = 50mA$
- Enhancement-Mode
- Complementary to 2SJ168.

Marking



MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current	DC	I_D	200
	Pulse	I_{DP}	800
Drain Power Dissipation (Ta = 25°C)	P_D	200	mW
Channel Temperature	T_{ch}	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C



Weight : 0.012g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Gate Leakage Current	I_{GSS}	$V_{GS} = \pm 10V, V_{DS} = 0$	—	—	± 100	nA	
Drain Cut-off Current	I_{DSS}	$V_{DS} = 60V, V_{GS} = 0$	—	—	10	μA	
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 1mA, V_{GS} = 0$	60	—	—	V	
Gate Threshold Voltage	V_{th}	$V_{DS} = 10V, I_D = 1mA$	2	—	3.5	V	
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10V, I_D = 50mA$	100	—	—	mS	
Drain-Source ON Resistance	$R_{DS(ON)}$	$I_D = 50mA, V_{GS} = 10V$	—	0.6	1.0	Ω	
Drain-Source ON Voltage	$V_{DS(ON)}$	$I_D = 50mA, V_{GS} = 10V$	—	30	50	mV	
Input Capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$	—	55	65	pF	
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$	—	13	18	pF	
Output Capacitance	C_{oss}	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$	—	40	50	pF	
Switching Time	Rise Time	t_r			—	8	—
	Turn-on Time	t_{on}			—	14	—
	Fall Time	t_f			—	35	—
	Turn-off Time	t_{off}			—	75	—

This transistor is the electrostatic sensitive device. Please handle with caution.



